

# MOSFET – Single, N-Channel, 2.5 V, Specified, POWERTRENCH®

20 V, 5.7 A, 30 mΩ

## FDMA420NZ

### General Description

This Single N-Channel MOSFET has been designed using onsemi's advanced POWERTRENCH process to optimize the  $R_{DS(on)}$  @  $V_{GS} = 2.5$  V on special MicroFET™ leadframe.

### Features

- $R_{DS(on)} = 30$  mΩ @  $V_{GS} = 4.5$  V,  $I_D = 5.7$  A
- $R_{DS(on)} = 40$  mΩ @  $V_{GS} = 2.5$  V,  $I_D = 5.0$  A
- Low Profile – 0.8 mm Maximum—in the New Package MicroFET 2x2 mm
- HBM ESD Protection Level > 2.5 kV Typical (Note 3)
- Free from Halogenated Compounds and Antimony Oxides
- This Device is Pb-Free, Halide Free and is RoHS Compliant

### Applications

- Li-Ion Battery Pack

### MOSFET MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

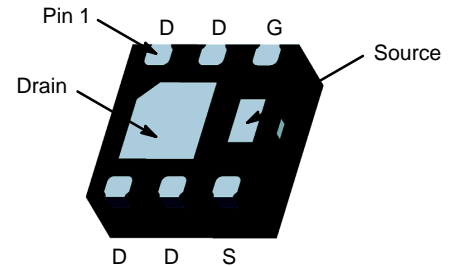
Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-Source Voltage	20	V
$V_{GSS}$	Gate-Source Voltage	±12	V
$I_D$	Drain Current – Continuous (Note 1a) – Pulsed	5.7 24	A
$P_D$	Power Dissipation (Steady State) (Note 1a) (Note 1b)	2.4 0.9	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

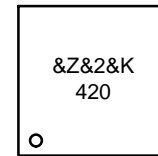
Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	

$V_{DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
20 V	30 mΩ @ 4.5 V	5.7 A
	40 mΩ @ 2.5 V	



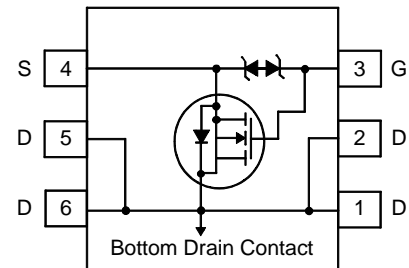
Bottom View  
WDFN6 2x2, 0.65P  
(MicroFET 2x2)  
CASE 511CZ

### MARKING DIAGRAM



&Z = Assembly Plant Code  
&2 = 2-Digit Date Code  
&K = 2-Digits Lot Run Traceability Code  
420 = Specific Device Code

### PIN ASSIGNMENT



### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# FDMA420NZ

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
--------	-----------	----------------	-----	-----	-----	------

### OFF CHARACTERISTICS

B <sub>V</sub> DSS	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20	–	–	V
$\frac{\Delta B_{V_{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	–	12	–	mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V	–	–	1	μA
I <sub>GSS</sub>	Gate–Body Leakage	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0 V	–	–	±10	μA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.6	0.83	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	–	–3.1	–	mV/°C
R <sub>DS(ON)</sub>	Static Drain–Source On–Resistance	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5.7 A	–	16.8	30	mΩ
		V <sub>GS</sub> = 4.0 V, I <sub>D</sub> = 5.7 A	–	17.3	31	
		V <sub>GS</sub> = 3.1 V, I <sub>D</sub> = 5.0 A	–	18.9	33	
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 5.0 A	–	21.2	40	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5.7 A, T <sub>J</sub> = 150°C	–	24.8	44	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 5.7 A	–	28.3	–	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	–	701	935	pF
C <sub>oss</sub>	Output Capacitance		–	163	220	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	125	190	pF
R <sub>G</sub>	Gate Resistance	f = 1.0 MHz	–	1.92	–	Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn–On Delay Time	V <sub>DD</sub> = 10 V, I <sub>D</sub> = 1 A, V <sub>GS</sub> = 4.5 V, R <sub>GEN</sub> = 6 Ω	–	9.8	20	ns
t <sub>r</sub>	Turn–On Rise Time		–	8.6	18	ns
t <sub>d(off)</sub>	Turn–Off Delay Time		–	21.5	43	ns
t <sub>f</sub>	Turn–Off Fall Time		–	8.6	18	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5.7 A, V <sub>GS</sub> = 4.5 V	–	8.8	12	nC
Q <sub>gs</sub>	Gate–Source Charge		–	0.9	2	nC
Q <sub>gd</sub>	Gate–Drain Charge		–	2.4	4	nC

### DRAIN–SOURCE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Drain–Source Diode Forward Current	–	–	2.0	A	
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.0 A	–	0.69	1.2	V
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 5.7 A, di/dt = 100 A/μs	–	–	20	ns
Q <sub>rr</sub>	Diode Reverse Recovery Charge		–	–	5	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- R<sub>θJA</sub> is the sum of the junction–to–case and case–to–ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.



a. 52°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 145°C/W when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
- The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

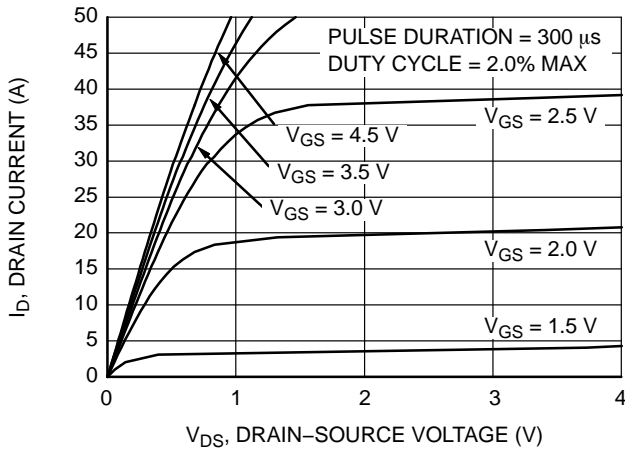


Figure 1. On Region Characteristics

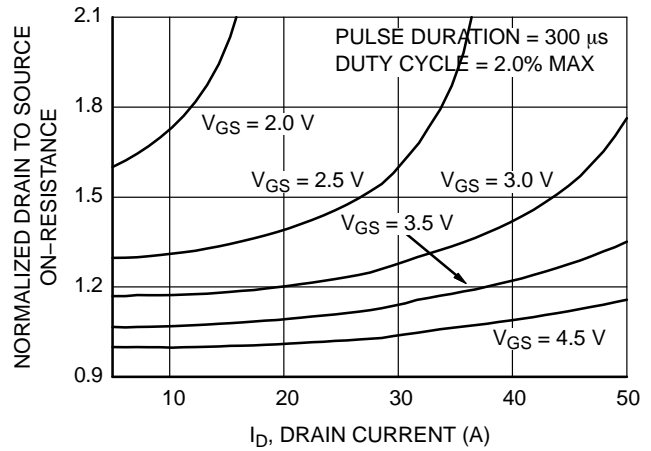


Figure 2. On-Resistance vs. Drain Current and Gate Voltage

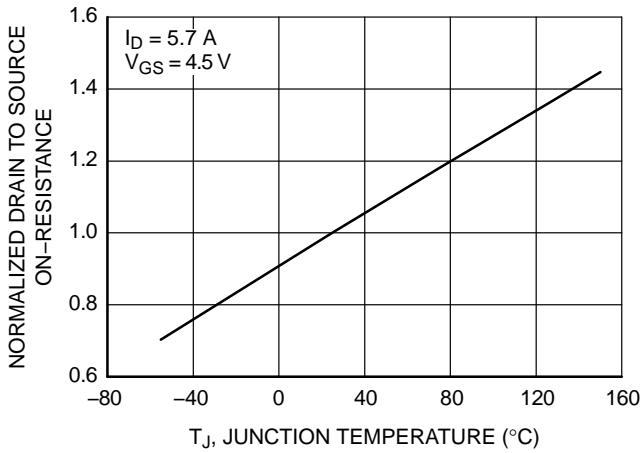


Figure 3. Normalized On Resistance vs. Junction Temperature

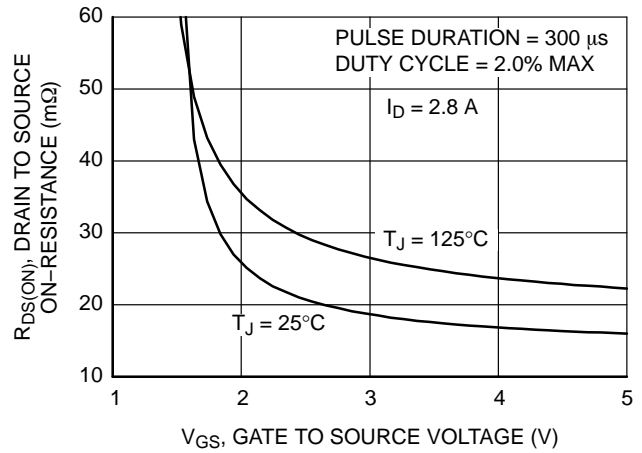


Figure 4. On-Resistance vs. Gate to Source Voltage

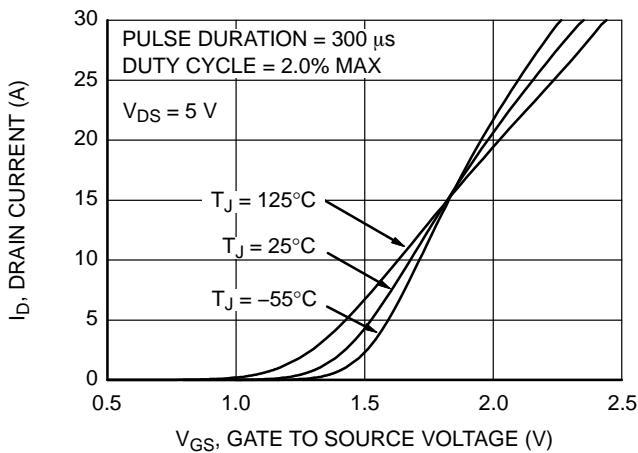


Figure 5. Transfer Characteristics

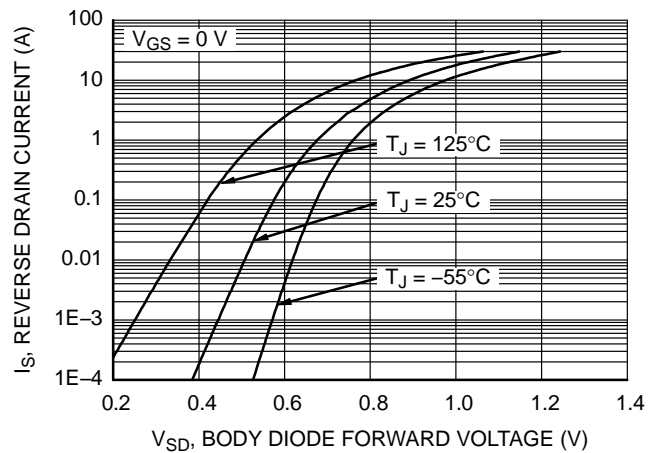


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (T<sub>J</sub> = 25°C, unless otherwise noted) (continued)

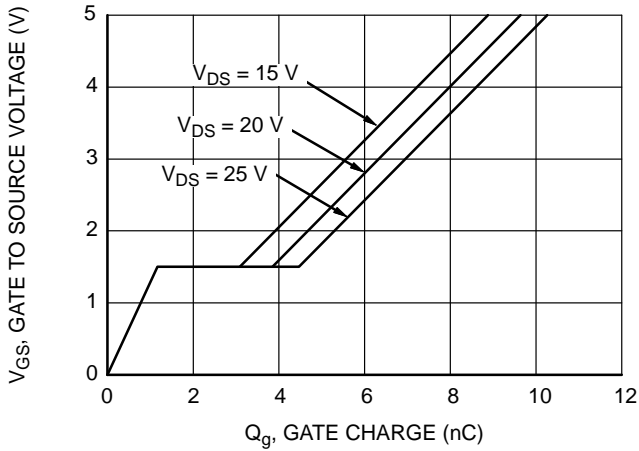


Figure 7. Gate Charge Characteristics

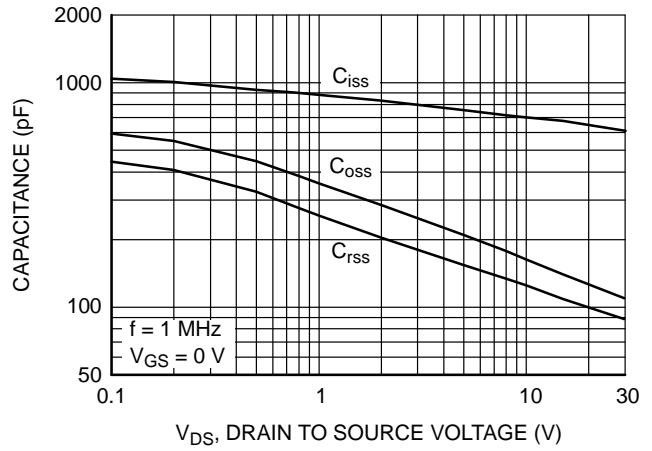


Figure 8. Capacitance vs. Drain to Source Voltage

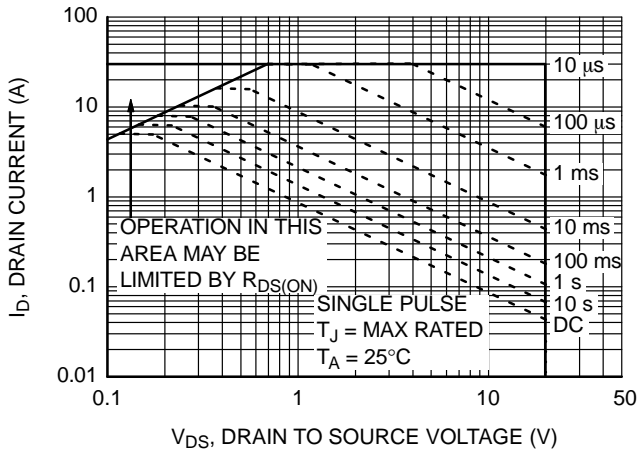


Figure 9. Forward Bias Safe Operating Area

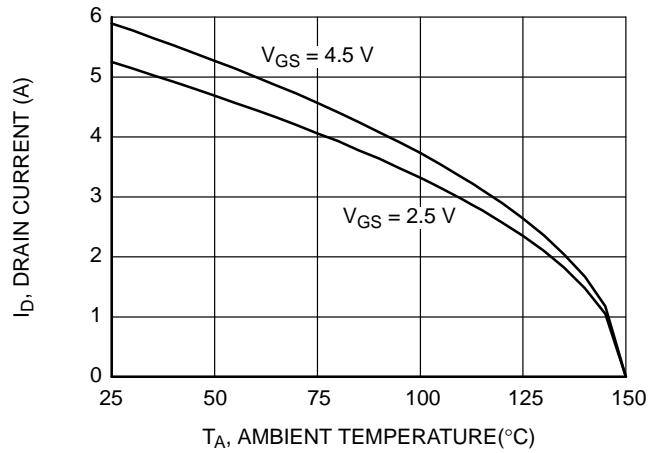


Figure 10. Maximum Continuous Drain Current vs. Ambient Temperature

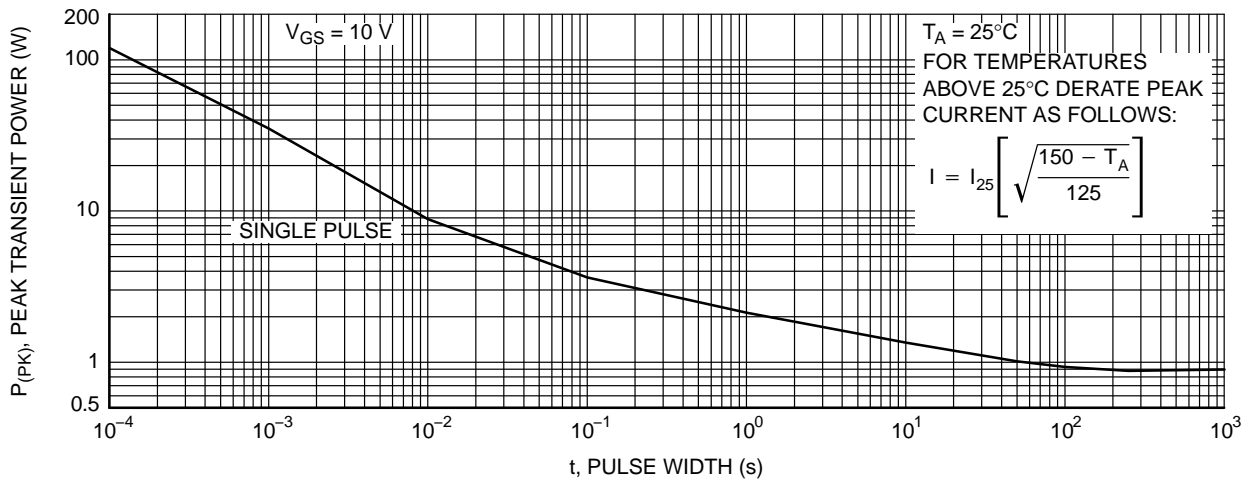


Figure 11. Single Pulse Maximum Power Dissipation

# FDMA420NZ

## TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise noted) (continued)

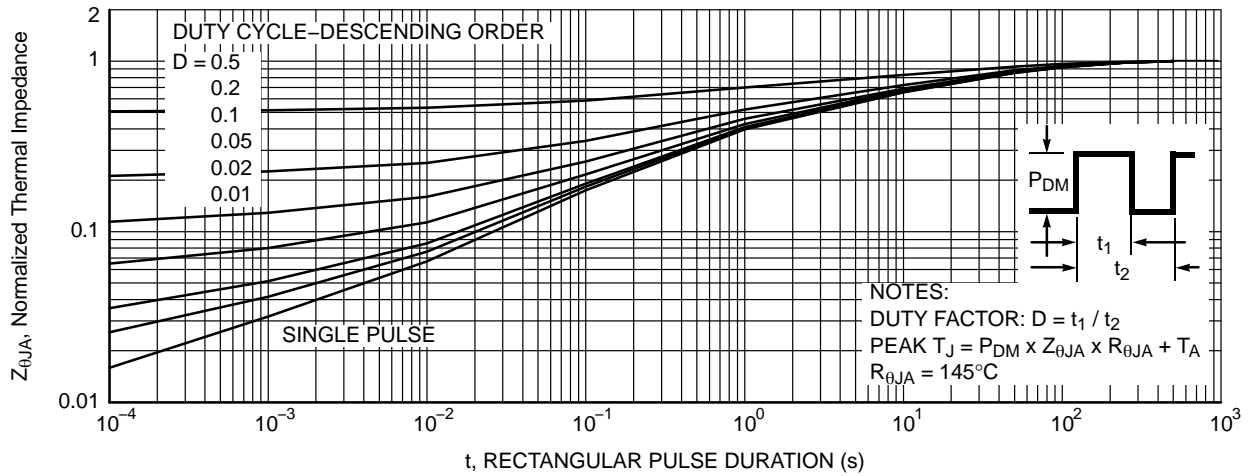


Figure 12. Transient Thermal Response Curve

### PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Shipping†
FDMA420NZ	420	WDFN6 2x2, 0.65P (MicroFET 2x2) (Pb-Free, Halide Free)	7"	8 mm	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

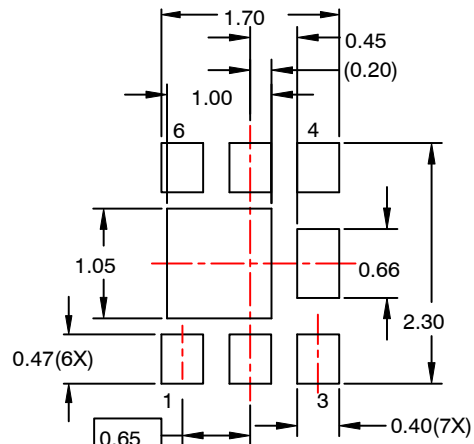
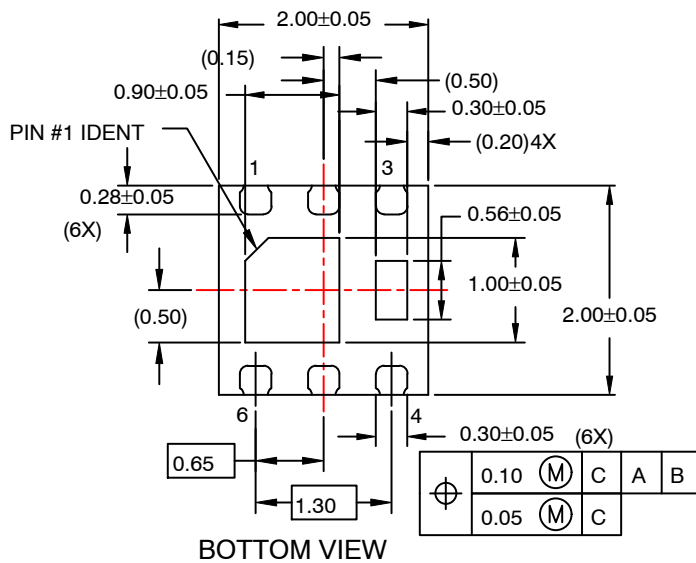
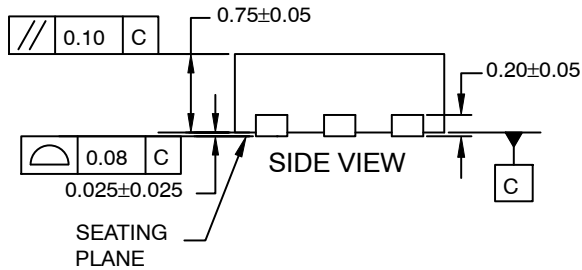
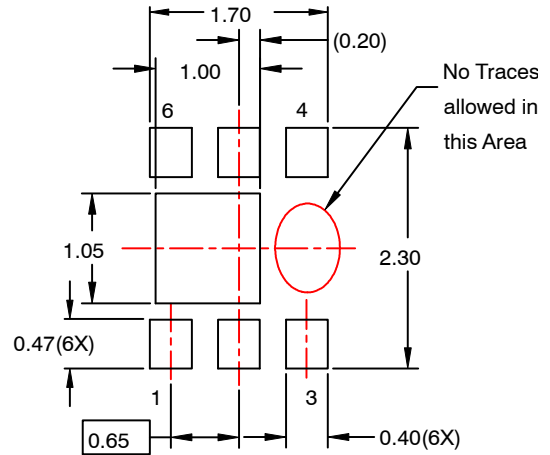
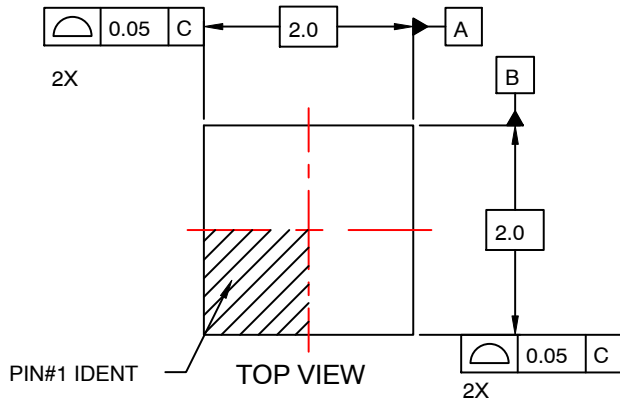
POWERTRENCH is registered trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.

MicroFET is trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.



**WDFN6 2x2, 0.65P**  
**CASE 511CZ**  
**ISSUE O**

DATE 31 JUL 2016



**NOTES:**

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

<b>DOCUMENT NUMBER:</b>	<b>98AON13614G</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>WDFN6 2X2, 0.65P</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

---

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at [www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)